RICHTEK®

RTQ2510-QT

1A, Low Noise, High PSRR, Low-Dropout Linear Regulator

1 General Description

The RTQ2510-QT is a high-performance positive low dropout (LDO) regulator designed for applications requiring very low dropout voltage and high Power Supply Ripple Rejection (PSRR) at up to 1A. The input voltage range is from 2.2V to 6V, and the output voltage is programmable as low as 0.8V. The P-MOSFET switch provides excellent transient response with only a 4.7μF ceramic output capacitor. The external enable control effectively reduces power dissipation during shutdown and further output noise immunity is achieved through a bypass capacitor on the NR pin. Additionally, the RTQ2510-QT features a precise 1.5% output regulation over line, load, and temperature variations. The device is available in the VDFN-8L 3x3 package and is specified from –40°C to 125°C.

2 Ordering Information

RTQ2510□-QT□

Packing
B: Pin 1 Orientation
(Quadrant 2, Follow EIA-481)

Grade
QT: AEC-Q100 Qualified and Screened by High Temperature

Package Type(1)
N: VDFN-8L 3x3 (V-Type)
Richtek Green Policy Compliant

Note 1.

Richtek products are Richtek Green Policy compliant and marked with (1) indicates compatible with the current requirements of IPC/JEDEC J-STD-020.

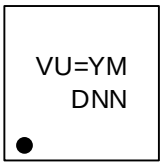
3 Features

- **AEC-Q100 Grade 1 Qualified**
- **Dropout: 170mV Typical at 1A**
- **PSRR: 63dB @ 1kHz, 38dB @ 1MHz**
- **Input Voltage Range: 2.2V to 6V**
- **Adjustable Output Voltage: 0.8V to 5.5V**
- **–40°C to 125°C Operating Junction Temperature Range**
- **Excellent Noise Immunity**
- **Fast Response Over Load and Line Transient**
- **Stable with a 4.7μF Output Ceramic Capacitor**
- **Accurate Output Voltage 1.5% Over Load, Line, Process, and Temperature Variations**
- **Enable Control**
- **Overcurrent Protection**
- **Over-Temperature Protection**

4 Applications

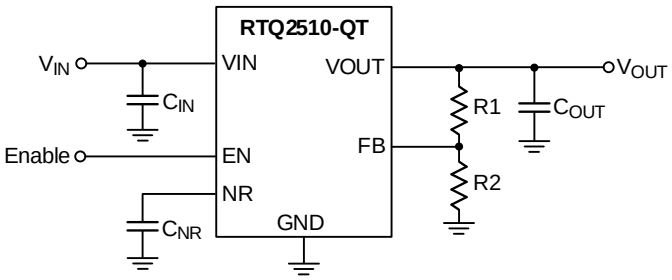
- In-Vehicle Infotainment Systems
- Telematics Control Units
- Instrument Clusters
- Automotive Head Units
- ADAS Camera and Radar
- Navigation Systems

5 Marking Information



VU= : Product Code
YMDNN : Date Code

6 Simplified Application Circuit



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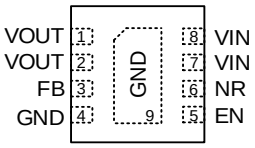
7 Pin Configuration

(TOP VIEW)

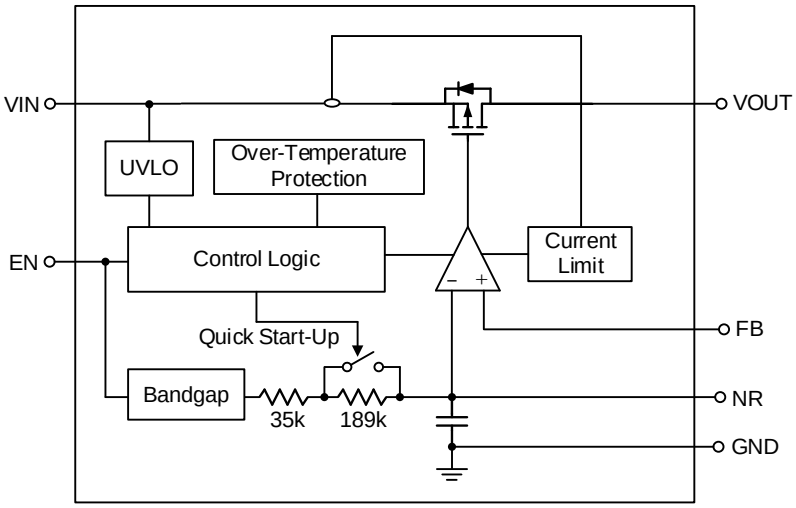


VDFN-8L 3x3

8 Functional Pin Description

Pin No.	Pin Name	Pin Function
1, 2	VOUT	Output of the regulator. Decouple this pin to GND with at least 4.7μF for stability.
3	FB	Feedback voltage input. This pin is used to set the desired output voltage via an external resistive divider. The feedback reference voltage is 0.8V typically.
4, 9 (Exposed Pad)	GND	System ground. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.
5	EN	Enable control input. Connecting this pin to logic high enables the regulator or driving this pin low puts it into shutdown mode. EN can be connected to IN if not used. (The EN pin is not allowed to be left floating.)
6	NR	Noise reduction input. Decoupling this pin to GND with an external capacitor cannot only reduce output noise to very low levels but also slow down the VOUT rise, like a soft-start behavior.
7, 8	VIN	Supply input. A minimum of 1μF ceramic capacitor should be placed as close as possible to this pin for better noise rejection.

9 Functional Block Diagram



10 Absolute Maximum Ratings

(Note 2)

- All Pins ---------- –0.3V to 7V
- Lead Temperature (Soldering, 10 sec.) ---------- 260°C
- Junction Temperature ---------- 150°C
- Storage Temperature Range ---------- –65°C to 150°C

Note 2. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

11 ESD Ratings

(Note 3)

- ESD Susceptibility
- HBM (Human Body Model)---------- 2kV

Note 3. Devices are ESD sensitive. Handling precautions are recommended.

12 Recommended Operating Conditions

(Note 4)

- Supply Input Voltage, VIN ---------- 2.2V to 6V
- Junction Temperature Range---------- –40°C to 125°C

Note 4. The device is not guaranteed to function outside its operating conditions.

13 Thermal Information

(Note 5 and Note 6)

Thermal Parameter		VDFN-8L 3x3	Unit
θ_{JA}	Junction-to-ambient thermal resistance (JEDEC standard)	60.82	°C/W
$\theta_{JC(Top)}$	Junction-to-case (top) thermal resistance	83.76	°C/W
$\theta_{JC(Bottom)}$	Junction-to-case (bottom) thermal resistance	10.48	°C/W
$\theta_{JA(EVB)}$	Junction-to-ambient thermal resistance (specific EVB)	45.06	°C/W
$\Psi_{JC(Top)}$	Junction-to-top characterization parameter	5.42	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	26.17	°C/W

Note 5. For more information about thermal parameter, see the Application and Definition of Thermal Resistances report, AN061.

Note 6. $\theta_{JA\ (EVB)}$, $\Psi_{JC(Top)}$, and Ψ_{JB} are measured on a high effective-thermal-conductivity four-layer test board, which is in size of 70mm x 50mm; furthermore, all layers with 1 oz. Cu. Thermal resistance/parameter values may vary depending on the PCB material, layout, and test environmental conditions.

14 Electrical Characteristics

(V_{IN} = V_{OUT} + 0.5V or 2.2V, V_{OUT} = 0.8V and 5.5V, I_{OUT} = 1mA, V_{EN} = 2.2V, C_{NR} = 10nF, C_{OUT} = 4.7µF, T_J = -40°C to 125°C, unless otherwise specified.)

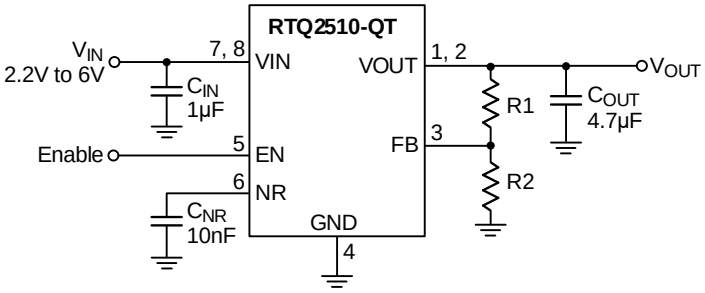
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Supply Voltage						
VIN Supply Input Voltage	V_{IN}		2.2	--	6	V
Undervoltage-Lockout Rising Threshold	V_{UVLO}	R_{OUT} = 1kΩ	1.86	2	2.1	V
Undervoltage-Lockout Hysteresis	V_{UVLO_HYS}	R_{OUT} = 1kΩ	--	200	--	mV
Shutdown Current	I_{SHDN}	V_{EN} ≤ 0.4V, V_{IN} ≥ 2.2V, R_{OUT} = 1kΩ, 0°C ≤ T_J ≤ 85°C	--	0.2	2	µA
		V_{EN} ≤ 0.4V, V_{IN} ≥ 2.2V, R_{OUT} = 1kΩ, –40°C ≤ T_J ≤ 125°C	--	0.2	5	
Quiescent Current	I_Q		--	190	350	µA
Output Voltage						
Output Voltage	V_{OUT}		0.8	--	5.5	V
Output Voltage Accuracy (Note 7)	V_{OUT_ACC}	V_{OUT} + 0.5V ≤ V_{IN} ≤ 6V, V_{IN} ≥ 2.5V, 100mA ≤ I_{OUT} ≤ 500mA, 0°C ≤ T_J ≤ 85°C	–1	--	1	%
		V_{OUT} + 0.5V ≤ V_{IN} ≤ 6V, V_{IN} ≥ 2.2V, 100mA ≤ I_{OUT} ≤ 1A –40°C ≤ T_J ≤ 125°C	–1.5	--	1.5	
Line Regulation	V_{LINE_REG}	V_{OUT} + 0.5V ≤ V_{IN} ≤ 6V, V_{IN} ≥ 2.2V, I_{OUT} = 100mA	--	0.2	--	%
Load Regulation	V_{LOAD_REG}	100mA ≤ I_{OUT} ≤ 1A	--	0.3	--	%
Enable Voltage						
EN Input Voltage Rising Threshold	V_{EN_R}	V_{EN} rising, 2.2V ≤ V_{IN} ≤ 6V, R_{OUT} = 1kΩ	1.2	--	--	V
EN Input Voltage Falling Threshold	V_{EN_F}	V_{EN} falling, R_{OUT} = 1kΩ	--	--	0.4	
EN Input Current	I_{EN}	V_{IN} = 6V, V_{EN} = 6V	--	0.02	1	µA
FB Input Current	I_{FB}	V_{IN} = 5.5V, V_{FB} = 0.8V	--	0.02	1	µA
Current Limit						
Current Limit	I_{LIM}	V_{IN} = 3.3V, V_{OUT} = 0.85 x V_{OUT}	1.1	1.4	2	A
Power-Up Time						
Soft-Start Time	t_{SS}	V_{OUT} = 3.3V, R_{OUT} = 3.3kΩ, C_{OUT} = 4.7µF, C_{NR} = 1nF	--	0.16	--	ms
		C_{NR} = 10nF	--	1.6	--	

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Dropout Voltage							
Dropout Voltage	V_{DROP}	V_{OUT} + 0.5V ≤ V_{IN} ≤ 6V, V_{FB} = 0V	V_{IN} ≥ 2.2V, I_{OUT} = 500mA	--	--	160	mV
			V_{IN} ≥ 2.5V, I_{OUT} = 750mA	--	--	210	
			V_{IN} ≥ 2.5V, I_{OUT} = 1A	--	--	370	
Power Supply Ripple Rejection and Noise							
Power Supply Ripple Rejection	PSRR	V_{IN} = 4.3V, V_{OUT} = 3.3V, I_{OUT} = 750mA (Note 8)	f = 100Hz	--	48	--	dB
			f = 1kHz	--	63	--	
			f = 10kHz	--	63	--	
			f = 1MHz	--	38	--	
Output Noise	V_n	BW = 100Hz to 100kHz, V_{IN} = 4.3V, V_{OUT} = 3.3V, I_{OUT} = 100mA (Note 8)	C_{NR} = 1nF	--	15.6 x V_{OUT}	--	μVRMS
			C_{NR} = 10nF	--	15.6 x V_{OUT}	--	
			C_{NR} = 0.1μF	--	15.1 x V_{OUT}	--	
Over-Temperature Protection							
Over-Temperature Protection Threshold	T_{OTP}	(Note 8)		--	160	--	°C
Over-Temperature Protection Hysteresis	T_{OTP_HYS}	(Note 8)		--	20	--	

Note 7. The spec does not cover the tolerances from external resistors, and which is not tested at condition of V_{OUT} = 0.8V, 4.5V ≤ V_{IN} ≤ 6V, and 750mA ≤ I_{OUT} ≤ 1A since the power dissipation of the device is totally higher than the maximum rating of the package to lead a thermal shutdown issue.

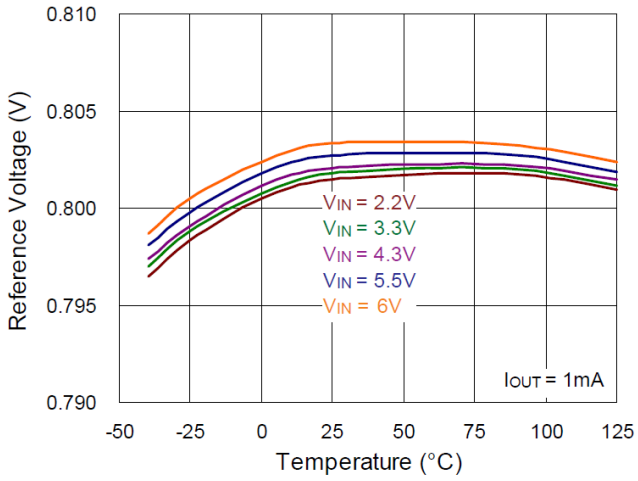
Note 8. Guarantee by design.

15 Typical Application Circuit

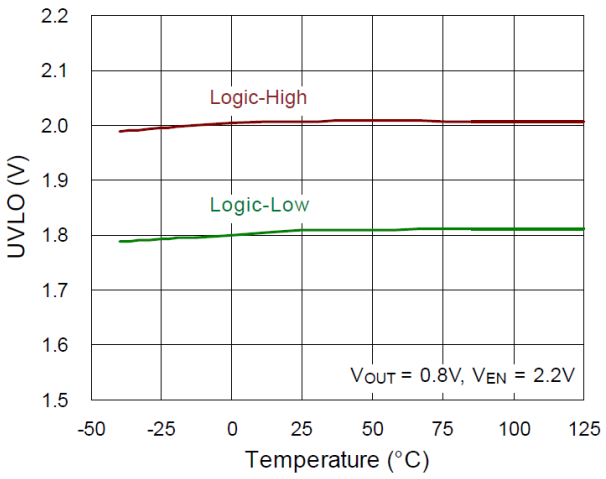


16 Typical Operating Characteristics

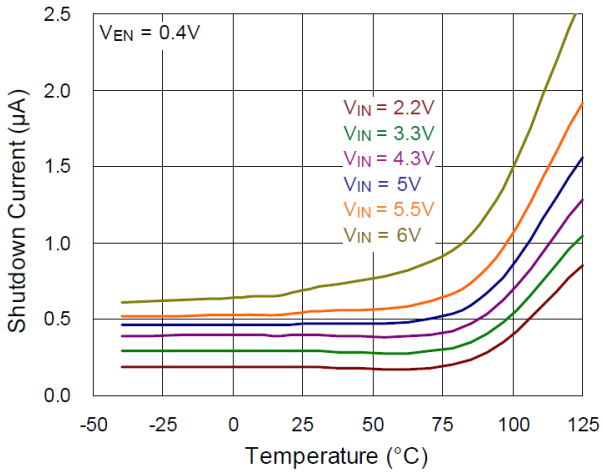
Reference Voltage vs. Temperature



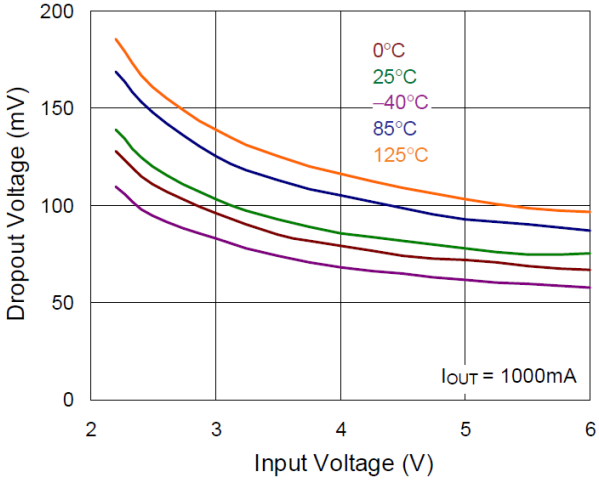
UVLO vs. Temperature



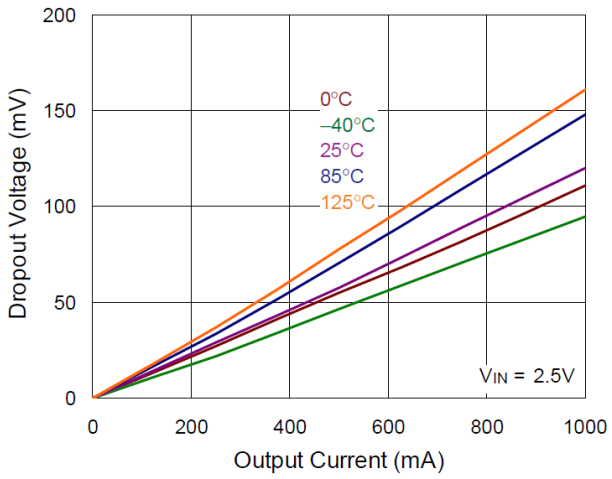
Shutdown Current vs. Temperature



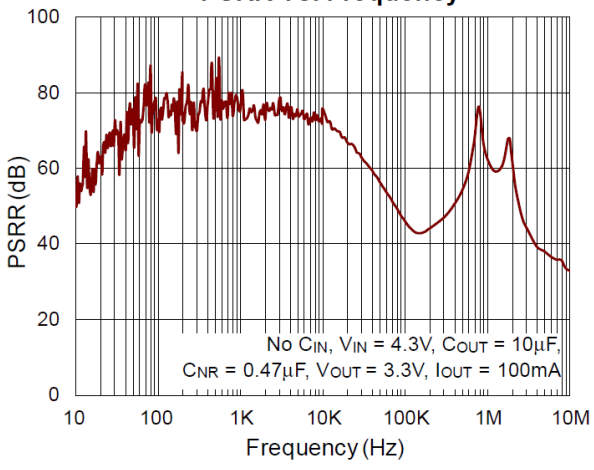
Dropout Voltage vs. Input Voltage



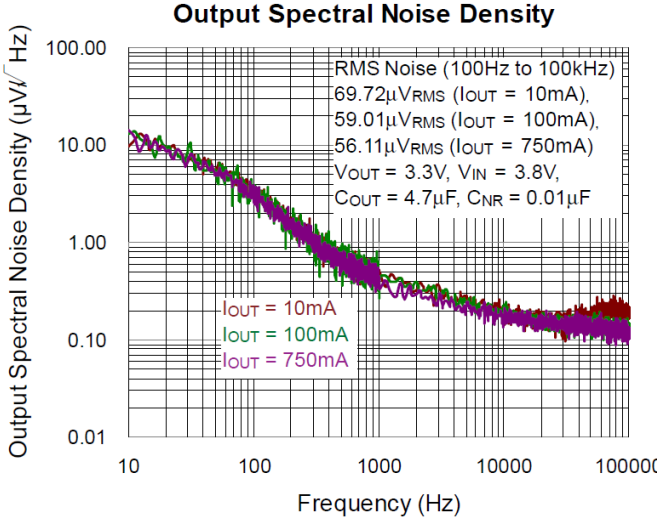
Dropout Voltage vs. Output Current



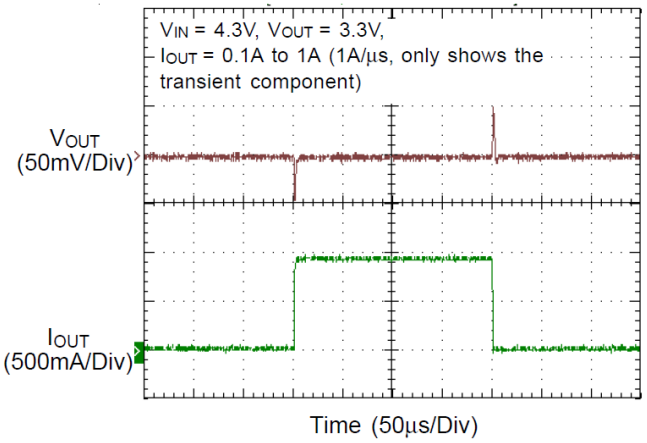
PSRR vs. Frequency



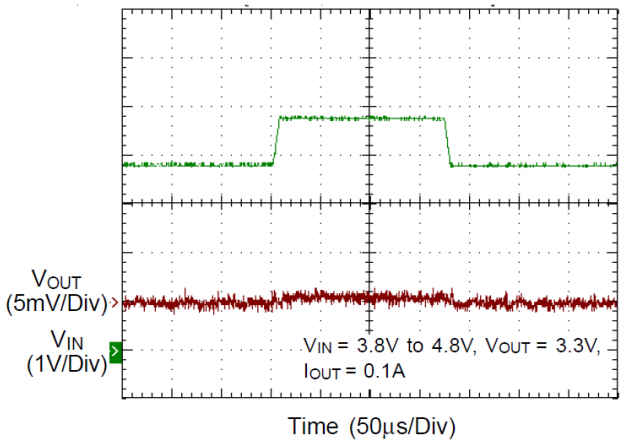
Output Spectral Noise Density



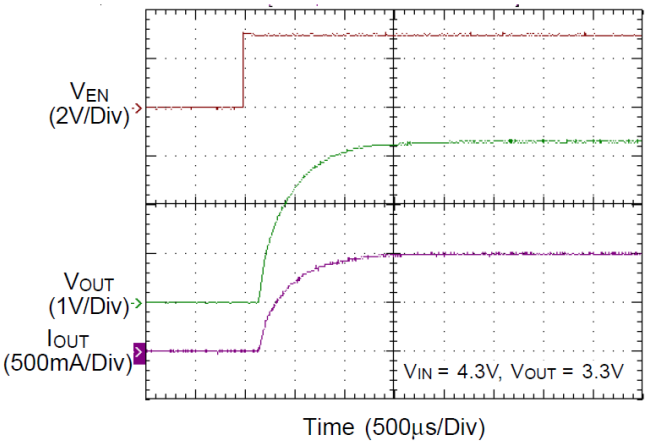
Load Transient Response



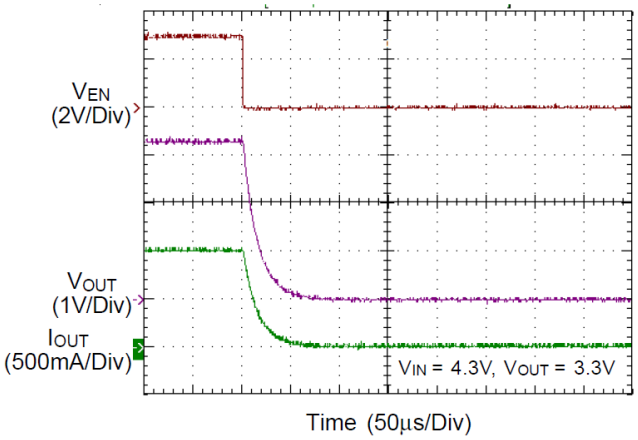
Line Transient Response



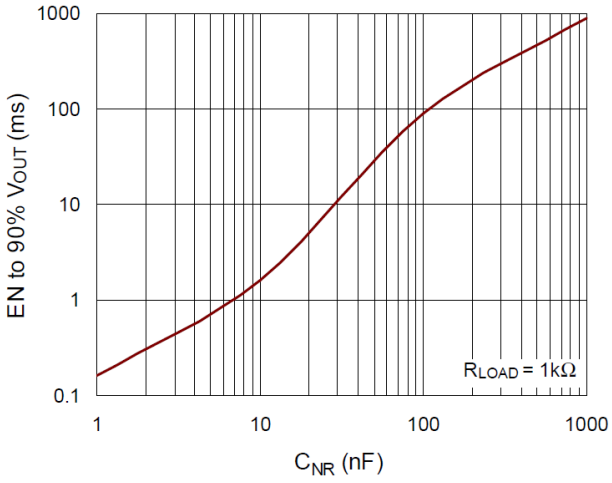
Power On from EN



Power Off from EN



Start-Up Time vs. Noise Reduction Capacitance



17 Operation

The RTQ2510-QT is a low noise, high PSRR LDO which supports very low dropout operation. The operating input voltage range is from 2.2V to 6V, the output voltage is programmable as low as 0.8V, and the output current can be up to 1A. The internal compensation network is well designed to achieve fast transient response with good stability.

In steady-state operation, the feedback voltage is regulated to the reference voltage by the internal regulator. When the feedback voltage signal is less than the reference, the output current passing through the power MOSFET will be increased. The additional current is sent to the output until the voltage level of the FB pin returns to the reference voltage.

Conversely, if the feedback voltage is higher than the reference, the power MOSFET current is decreased. The excess charge at the output can be released by the loading current.

17.1 Start-Up

The RTQ2510-QT has a quick-start circuit to charge the noise reduction capacitor (C_{NR}). The switch of the quick-start circuit is closed at start-up.

To reduce the noise from the bandgap, there is a low-pass (RC) filter consisting of the C_{NR} and the resistor, which is connected with the bandgap, as shown in Functional Block Diagram.

At the start-up, the quick-start switch is closed, with only 35kΩ resistance between the bandgap and the NR pin. The quick-start switch opens approximately 2ms after the device is enabled, and the resistance between NR and the bandgap is about 224kΩ to form a very good low-pass filter with great noise reduction performance.

The 35kΩ resistance is used to slow down the reference voltage ramp to avoid inrush current at chip start-up, and the start-up time can be calculated using the following equation:

t_{SS} (sec) = 160000 x C_{NR} (F)

It is recommended that the C_{NR} value be larger than 0.01μF to reduce noise, and low-leakage ceramic capacitors are suitable. However, if the C_{NR} value is too large, the start-up time will be extended significantly if the C_{NR} is not fully charged within 2ms and the quick-start switch is opened. The C_{NR} will be charged through a higher resistance of 224kΩ, which will take much longer to complete the start-up process.

17.2 Enable and Shutdown Operation

The RTQ2510-QT enters shutdown mode when the EN pin is at a logic low condition. In this condition, the pass transistor, the error amplifier, and the bandgap are all turned off, reducing the supply current to 2μA (maximum). If the shutdown mode is not needed, the EN pin can be directly tied to the VIN pin to keep the LDO on.

17.3 Overcurrent Protection

The RTQ2510-QT continuously monitors the output current to protect the pass transistor against abnormal operations. When an overload or short circuit is encountered, the current limit circuitry controls the pass transistor's gate voltage to limit the output within the predefined range. Due to the built-in body diode, the pass transistor conducts current when the output voltage exceeds the input voltage. Since the current is not limited, external current protection should be added if the device may work at a reverse voltage state.

17.4 Over-Temperature Protection (OTP)

The RTQ2510-QT has an over-temperature protection. When the device triggers the OTP, the device shuts down until the temperature returns to a normal state.

17.5 Undervoltage-Lockout (UVLO)

The RTQ2510-QT utilizes an undervoltage-lockout circuit to keep the output shutdown until the internal circuitry is operating properly. The UVLO circuit has a de-glitch feature that typically ignores undershoot transients on the input if they are less than 30μs duration.

18 Application Information

(Note 9)

The RTQ2510-QT is a low voltage, low dropout linear regulator with an input voltage from 2.2V to 6V and an adjustable output voltage from 0.8V to 5.5V.

18.1 Dropout Voltage

The dropout voltage refers to the voltage difference between the VIN and VOUT pins while operating at a specific output current. The dropout voltage V_{DROP} can also be expressed as the voltage drop across the pass-FET at a specific output current (I_{RATED}) while the pass-FET is fully operating at the ohmic region, and the pass-FET can be characterized as a resistance R_{DSON}. Thus, the dropout voltage can be defined as ($V_{DROP} = V_{VIN} – V_{VOUT} = R_{DSON} \times I_{RATED}$).

For normal operation, the suggested LDO operating range is ($V_{VIN} > V_{VOUT} + V_{DROP}$) for good transient response and PSRR ability. Conversely, operating in the ohmic region will severely degrade these performances.

18.2 Output Voltage Setting

For the RTQ2510-QT, the output voltage is set by the voltage on the FB pin and is determined by the values of R1 and R2. The values of R1 and R2 can be calculated for any voltage using the following equation:

$$V_{OUT} = \frac{(R1 + R2)}{R2} \times 0.8$$

It is recommended to use lower values for R1 and R2 to reduce the noise injected from the FB pin. Note that R1 is connected from the VOUT pin to the FB pin, and R2 is connected from FB to GND.

18.3 Chip Enable Operation

The EN pin is the chip enable input. Pulling the EN pin low (<0.4V) will shut down the device. During shutdown mode, the RTQ2510-QT quiescent current drops to lower than 2μA. Driving the EN pin high (>1.2V, <6V) will turn on the device again. For external timing control (for example, RC), the EN pin can also be externally pulled high by adding a 100kΩ or greater resistor from the VIN pin.

18.4 Overcurrent Protection

The RTQ2510-QT continuously monitors the output current to protect the pass transistor against abnormal operations. When an overload or short circuit is encountered, the current limit circuitry controls the pass transistor's gate voltage to limit the output within the predefined range. Due to the built-in body diode, the pass transistor conducts current when the output voltage exceeds the input voltage. Since the current is not limited, external current protection should be added if the device may operate at a reverse voltage state.

18.5 C_{IN} and C_{OUT} Selection

Like any low dropout regulator, the external capacitors of the RTQ2510-QT must be carefully selected for regulator stability and performance. Using a capacitor of at least 4.7μF is suitable. The input capacitor must be located at a distance of no more than 0.5 inch from the input pin of the chip. Any good quality ceramic capacitor can be used. However, a capacitor with larger value and lower ESR (Equivalent Series Resistance) is recommended since it will provide better PSRR and line transient response.

The RTQ2510-QT is designed specifically to work with low ESR ceramic output capacitor for space saving and performance considerations. Using a ceramic capacitor with a capacitance of at least 4.7μF on the RTQ2510-QT output ensures stability.

18.6 Output Noise

The dominant noise source is from the internal bandgap for most LDOs. With the noise reduction capacitor connected to the NR pin of the RTQ2510-QT, the noise component contributed from the bandgap will not be significant. Instead, the most significant noise source comes from the output resistor divider and the error amplifier input. For general noise reduction in applications, it is recommended to use a 0.01μF noise-reduction capacitor (C_{NR}).

18.7 Thermal Considerations

Thermal protection limits power dissipation in the RTQ2510-QT. When the operating junction temperature exceeds 160°C, the OTP circuit initiates the thermal shutdown function and turns off the pass element. The pass element turns on again after the junction temperature decreases by 20°C.

The RTQ2510-QT output voltage will be close to zero when an output short circuit occurs, as shown in Figure 1. This can reduce the IC temperature and provide maximum safety to end users when an output short circuit occurs.

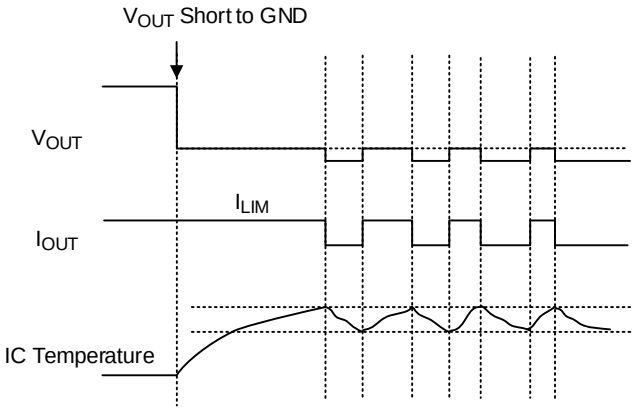


Figure 1. Short-Circuit Protection when Output Short-Circuit Occurs

The junction temperature should never exceed the absolute maximum junction temperature $T_{J(MAX)}$, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula:

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, $\theta_{JA(EVB)}$, is highly package dependent. For a VDFN-8L 3x3 package, the thermal resistance, $\theta_{JA(EVB)}$, is 45.06°C/W on a standard JEDEC 51-7 high effective-thermal-conductivity four-layer test board. The maximum power dissipation at T_A = 25°C can be calculated as follows:

$P_{D(MAX)}$ = (125°C – 25°C)/(45.06°C/W) = 2.22W for a VDFN-8L 3x3 package.

The maximum power dissipation depends on the operating ambient temperature for the fixed $T_{J(MAX)}$ and the thermal resistance, $\theta_{JA(EVB)}$. The derating curve in Figure 2 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

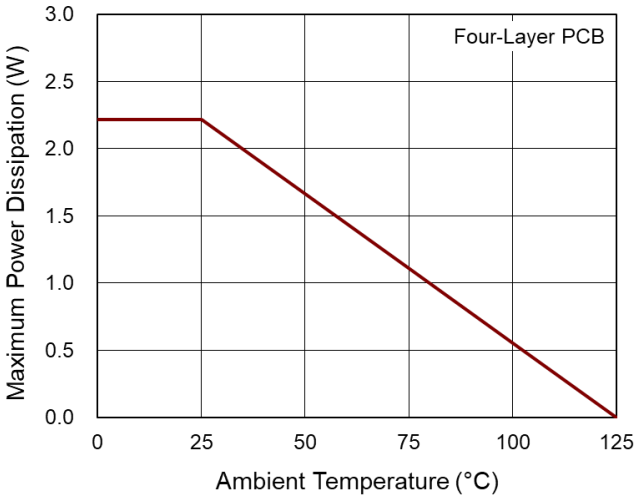


Figure 2. Derating Curve of Maximum Power Dissipation

18.8 Layout Considerations

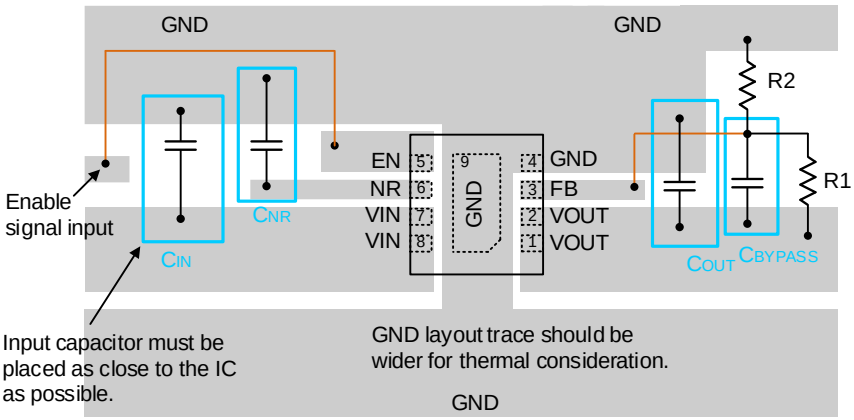
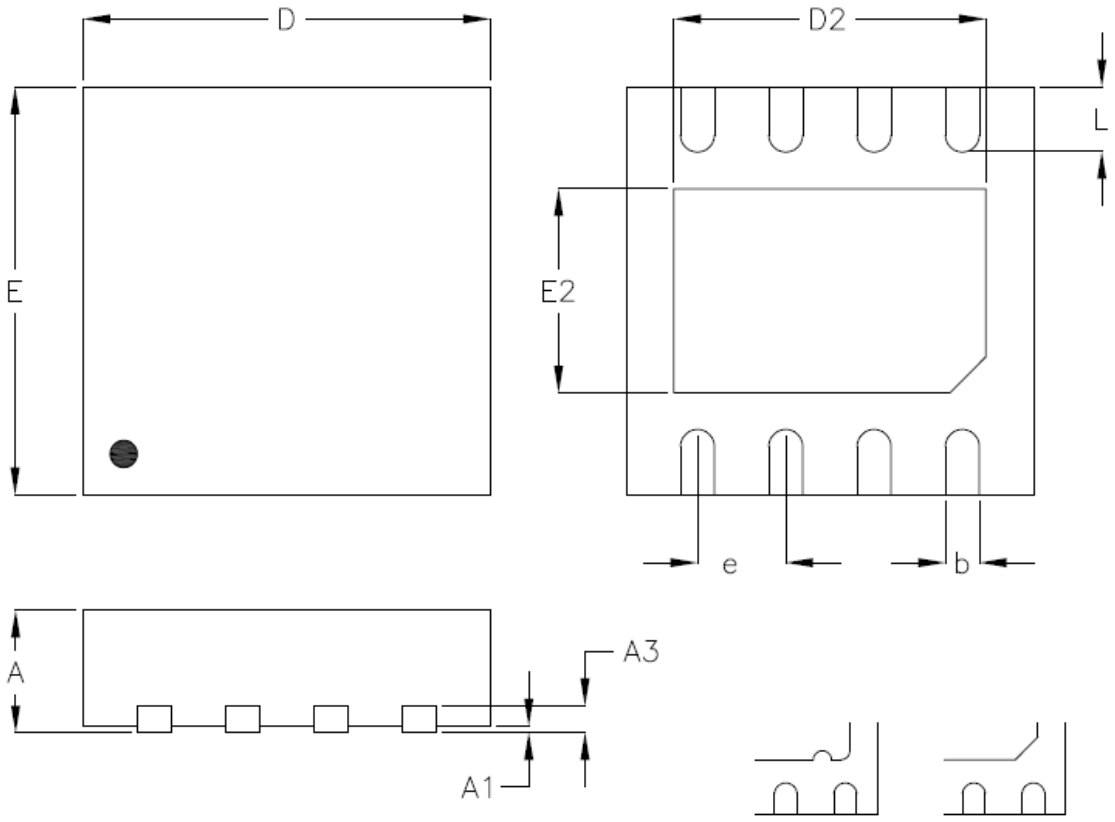


Figure 3. PCB Layout Guide

Note 9. The information provided in this section is for reference only. The customer is solely responsible for the designing, validating, and testing your product incorporating Richtek's product and ensure such product meets applicable standards and any safety, security, or other requirements.

19 Outline Dimension

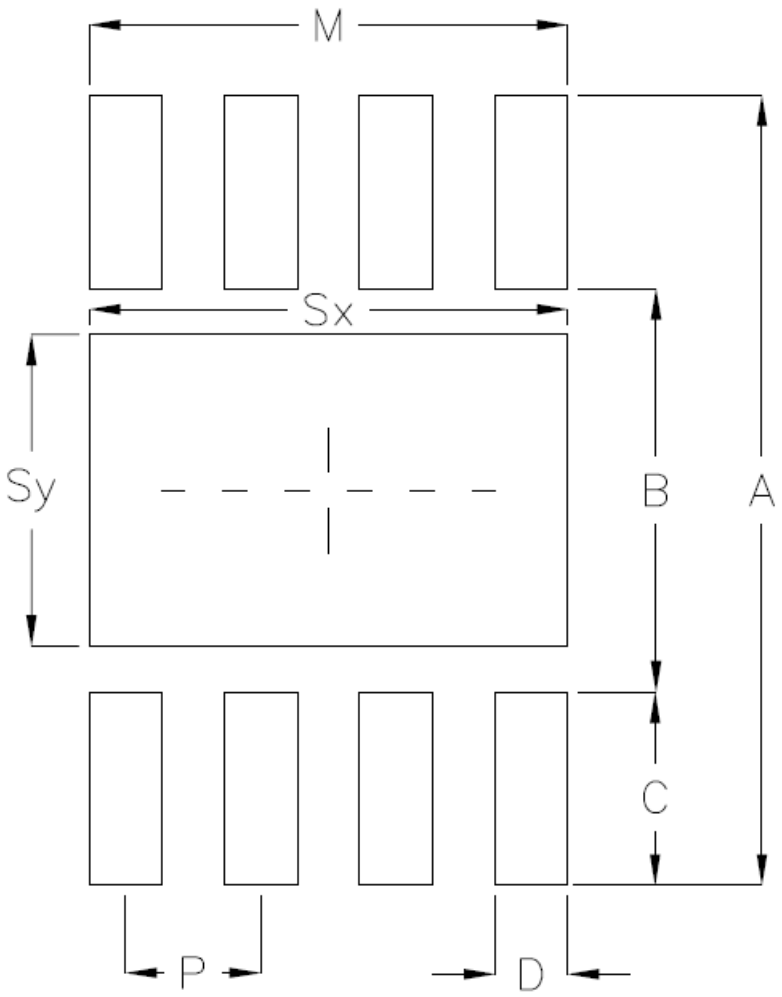


Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.027	0.035
A1	0.000	0.050	0.000	0.002
A3	0.175	0.250	0.007	0.010
b	0.200	0.300	0.008	0.012
D	2.950	3.050	0.116	0.120
D2	2.100	2.350	0.083	0.093
E	2.950	3.050	0.116	0.120
E2	1.350	1.600	0.053	0.063
e	0.650		0.026	
L	0.425	0.525	0.017	0.021

V-Type 8L DFN 3x3 Package

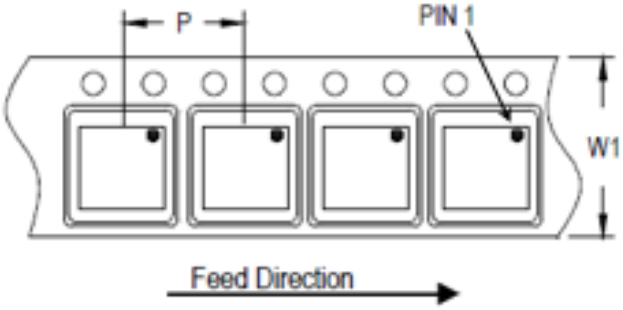
20 Footprint Information

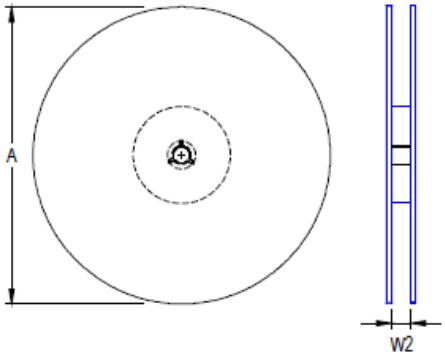


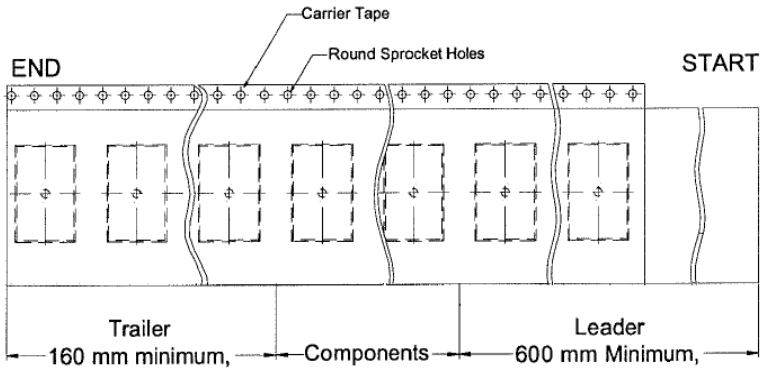
Package	Number of Pin	Footprint Dimension (mm)								Tolerance
		P	A	B	C	D	Sx	Sy	M	
V/W/U/XDFN3*3-8	8	0.65	3.80	1.94	0.93	0.35	2.30	1.50	2.30	±0.05

21 Packing Information

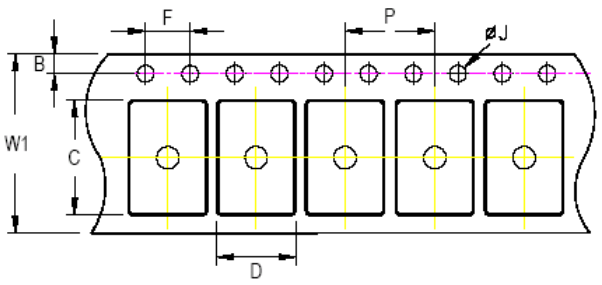
21.1 Tape and Reel Data







Package Type	Tape Size (W1) (mm)	Pocket Pitch (P) (mm)	Reel Size (A)		Units per Reel	Trailer (mm)	Leader (mm)	Reel Width (W2) Min/Max (mm)
			(mm)	(in)				
(V, W) QFN/DFN 3x3	12	8	180	7	1,500	160	600	12.4/14.4



C, D, and K are determined by component size. The clearance between the components and the cavity is as follows:

- For 12mm carrier tape: 0.5mm maximum

Tape Size	W1	P		B		F		ØJ		K		H
	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Max
12mm	12.3mm	7.9mm	8.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	1.0mm	1.3mm	0.6mm

21.2 Tape and Reel Packing

Step	Photo/Description	Step	Photo/Description
1	 Reel 7”	4	 3 reels per inner box **Box A**
2	 HIC & Desiccant (1 Unit) inside	5	 12 inner boxes per outer box
3	 Caution label is on backside of Al bag	6	 Outer box **Carton A**

Container / Package	Reel		Box			Carton		
	Size	Units	Item	Reels	Units	Item	Boxes	Unit
(V, W) QFN/DFN 3x3	7”	1,500	Box A	3	4,500	Carton A	12	54,000
			Box E	1	1,500	For Combined or Partial Reel.		

21.3 Packing Material Anti-ESD Property

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
Ω/cm^2	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}

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22 Datasheet Revision History

Version	Date	Description	Item
03	2025/8/6	First Edition	
04	2025/1/10	Modify	*General Description on page 1* *Features on page 1* *Simplified Application Circuit on page 2* *Electrical Characteristics on page 7* *Operation on page 12* *Application Information on page 15*